

DTC114EB / DTC114EM / DTC114EE / DTC114EUA / DTC114EKA

●Applications

Inverter, Interface, Driver

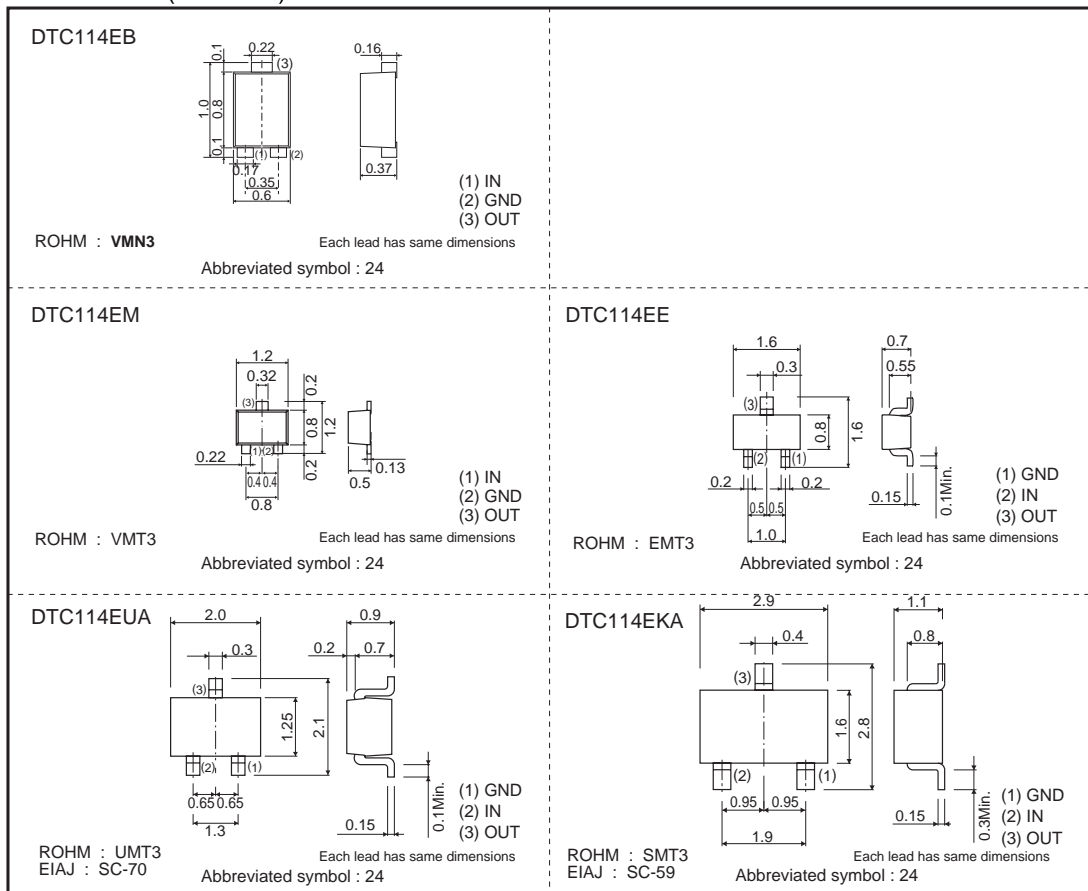
●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

●Structure

NPN epitaxial planar silicon transistor (Resistor built-in type)

●Dimensions (Unit : mm)

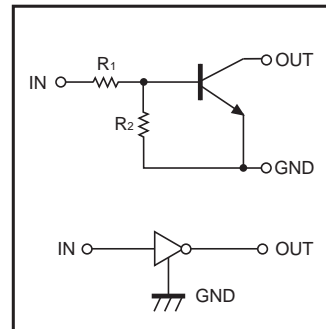


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●Packaging specifications

Part No.	Package	VMN3	VMT3	EMT3	UMT3	SMT3
	Packaging type	Taping	Taping	Taping	Taping	Taping
	Code	T2L	T2L	TL	T106	T146
	Basic ordering unit (pieces)	8000	8000	3000	3000	3000
DTC114EB	○	-	-	-	-	-
DTC114EM	-	○	-	-	-	-
DTC114EE	-	-	○	-	-	-
DTC114EUA	-	-	-	○	-	-
DTC114EKA	-	-	-	-	-	○

●Equivalent circuit



R<sub>1</sub>=R<sub>2</sub>=10kΩ

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits					Unit
		DTC114EB	DTC114EM	DTC114EE	DTC114EUA	DTC114EKA	
Supply voltage	V <sub>CC</sub>	50					V
Input voltage	V <sub>IN</sub>	-10 to +40					V
Output current	I <sub>O</sub>	50					mA
	I <sub>C(Max.)</sub>	100					
Power dissipation	P <sub>D</sub>	150		200			mW
Junction temperature	T <sub>J</sub>	150					°C
Storage temperature	T <sub>stg</sub>	-55 to +150					°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V <sub>I(off)</sub>	-	-	0.5	V	V <sub>CC</sub> =5V, I <sub>O</sub> =100μA
	V <sub>I(on)</sub>	3	-	-		V <sub>O</sub> =0.3V, I <sub>O</sub> =10mA
Output voltage	V <sub>O(on)</sub>	-	0.1	0.3	V	I <sub>O</sub> /I <sub>I</sub> =10mA/0.5mA
Input current	I <sub>I</sub>	-	-	0.88	mA	V <sub>I</sub> =5V
Output current	I <sub>O(off)</sub>	-	-	0.5	μA	V <sub>CC</sub> =50V, V <sub>I</sub> =0V
DC current gain	G <sub>I</sub>	30	-	-	-	V <sub>O</sub> =5V, I <sub>O</sub> =5mA
Input resistance	R <sub>1</sub>	7	10	13	kΩ	-
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	-	-
Transition frequency	f <sub>T</sub> *	-	250	-	MHz	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz

\* Characteristics of built-in transistor